

## Register Descriptions

The register descriptions section describes the behavior and function of the customer-programmable non-volatile-memory registers in the 9FGV1005 clock generator.

For details of product operation, refer to the product datasheet.

## 9FGV1005 Clock Register Set

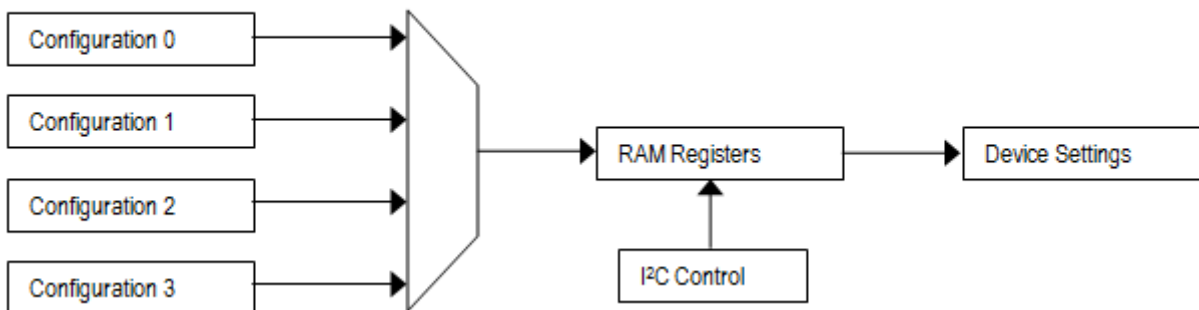
The device contains volatile (RAM) 8-bit registers and non-volatile 8-bit registers (Figure 1). The non-volatile registers are One-Time Programmable (OTP) and will be pre-programmed at the factory with a custom dash-code configuration.

The device operates according to settings in the RAM registers. At power-up a pre-programmed configuration is transferred from OTP to RAM registers. The device behavior can then be modified by reprogramming the RAM registers through I<sup>2</sup>C.

The device can start up in “I<sup>2</sup>C mode” or in “Hardware Select Mode”, depending upon the status of the REF0\_SEL\_I2C# pin at power up. Also see the datasheet. I<sup>2</sup>C access is only possible when the device has started up in I<sup>2</sup>C mode. Startup in I<sup>2</sup>C mode is default when no pull-up is added to the REF0\_SEL\_I2C# pin. Pre-programming settings determine which of the 4 OTP banks is loaded into RAM registers at power up in I<sup>2</sup>C mode. Using I<sup>2</sup>C commands, the configuration can be changed and there are also commands to reload a configuration from a different OTP bank.

Figure 1. Register Maps

### OTP Banks



## User Configuration Table Selection

At power-up, the voltage at OUT0\_SEL\_I2CB pin 24 is latched by the part and used to select the state of SEL0/SCL and SEL1/SDA pins (Table 1).

When a weak pull-up (10kΩ) is placed on REF0\_SEL\_I2C#, the SEL0/SCL and SEL1/SDA pins will be configured as hardware select inputs, SEL0 and SEL1. Connecting SEL0 and SEL1 to VDD and/or GND selects one of 4 configuration register sets, CFG0 through CFG3, which is then loaded into the non-volatile configuration registers to configure the clock synthesizer. The CFG0 through CFG3 configurations are preprogrammed at the factory according to customer specifications and assigned a specific (dash) part number.

When a weak pull-down is placed on REF0\_SEL\_I2C# (or when it is left floating to use internal pull-down), the pins SEL0 and SEL1 will be configured as an I<sup>2</sup>C interface's SDA and SCL slave bus. Configuration register set CFG0 is commonly loaded into the non-volatile configuration registers to configure the clock synthesizer but the device can be configured to load any of the other configurations. The host system can use the I<sup>2</sup>C bus to update the volatile RAM registers to change the configuration, and to read status registers.

Table 1. Power-Up Setting of Hardware Select Pin vs I<sup>2</sup>C Mode, and Default OTP Configuration Register

OUT0_SEL_I2CB Strap at Power-Up	SEL1/SDA pin	SEL0/SCL pin	Function
10kΩ pull-up	0	0	OTP bank CFG0 used to initialize RAM configuration registers.
	0	1	OTP bank CFG1 used to initialize RAM configuration registers.
	1	0	OTP bank CFG2 used to initialize RAM configuration registers.
	1	1	OTP bank CFG3 used to initialize RAM configuration registers.
10kΩ pull-down or floating	SDA	SCL	I <sup>2</sup> C bus enabled to access registers. OTP bank CFG0 used to initialize RAM configuration registers.

## I<sup>2</sup>C Interface and Register Access

When powered up in I<sup>2</sup>C mode, the device allows access to internal RAM registers. The default device address is 0xD0 for 8 bits or 0x68 for 7 bits. The device can be preprogrammed for addresses in the range 0xD0-D2-D4-D6 for 8 bits or 0x68-69-6A-6B for 7 bits. The device acts as a slave device on the I<sup>2</sup>C bus using one of the four I<sup>2</sup>C addresses to allow multiple devices to be used in the system. The interface accepts byte-oriented block write and block read operations. Two address bytes specify the register address of the byte position of the first register to write or read. Data bytes (registers) are accessed in sequential order from the lowest to the highest byte (most significant bit first). Read and write block transfers can be stopped after any complete byte transfer. During a write operation, data will not be moved into the registers until the STOP signal is received, at which point, all data received in the block write will be written simultaneously in the registers.

For full electrical I<sup>2</sup>C compliance, it is recommended to use external pull-up resistors for SDATA and SCLK. The internal pull-up resistors have a size of 100kΩ typical.

Figure 2. I<sup>2</sup>C R/W Sequence

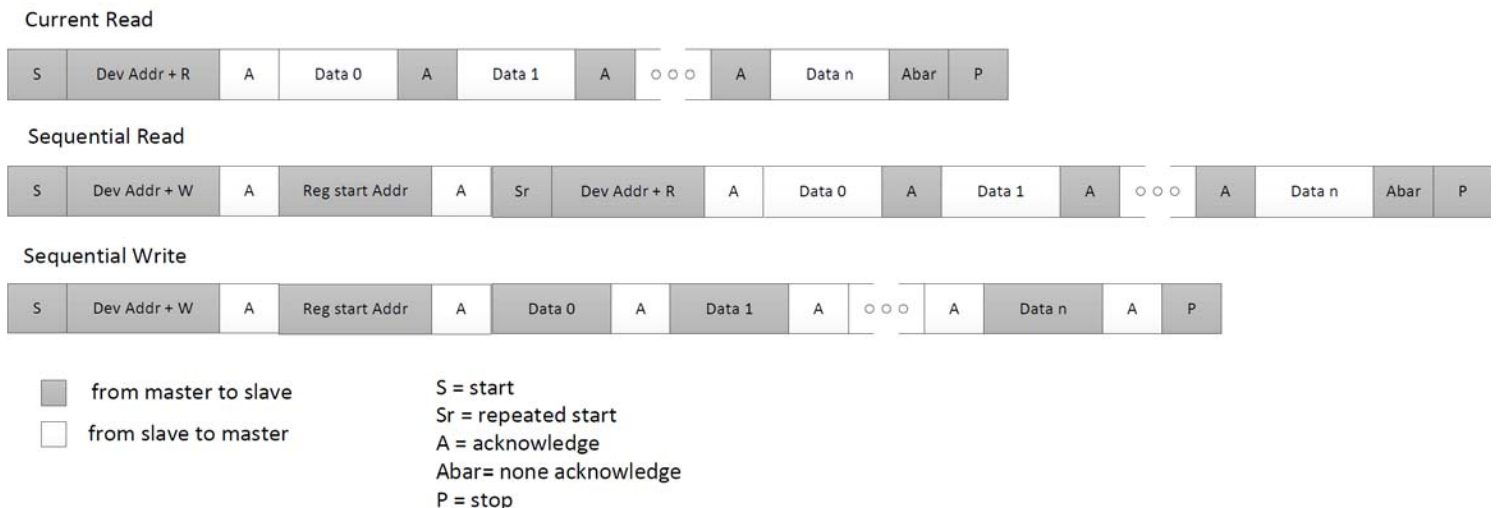


Table 2. RAM Overview

Register Address	Function Description
0x00	Device / I <sup>2</sup> C settings.
0x01	REF output settings.
0x02	Reserved.
0x03	
0x04	
0x05	OUT1 output settings.
0x06	
0x07	
0x08	Reserved.
0x09	
0x0A	
0x0B	OUT0 output settings.
0x0C	
0x0D	
0x0E	Crystal oscillator settings.
0x0F	
0x10	Reserved.
0x11	
0x12	
0x13	
0x14	
0x15	
0x16	
0x17	
0x18	
0x19	
0x1A	PLL miscellaneous.
0x1B	
0x1C	PLL loop filter settings.
0x1D	
0x1E	
0x1F	PLL feedback divider value.

Table 2. RAM Overview

Register Address	Function Description
0x20	Integer output divider values.
0x21	
0x22	
0x23	Reserved.
0x24	Reserved.
0x25	Miscellaneous device settings.

See [Table 3](#) for details at the bit level.

Table 3. RAM Register Map

Register Address		Register Bit	Default	Function Description
Decimal	Hex			
00	0x00	7	0	Device preprogrammed? 0 = No, 1 = Yes.
		[6..5]	00	I <sup>2</sup> C device address. 00 = 0xD0 / 0x68, 01 = 0xD2 / 0x69, 10 = 0xD4 / 0x6A, 11 = 0xD6 / 0x6B <sup>1</sup> .
		[4..2]	00	Reserved.
		[1..0]	00	Load configuration number at power-up <sup>2</sup> .
01	0x01	[7..6]	01	Enable REF outputs: 0x = REF0 disabled (unused), 10 = REF0 enabled.
		5	0	Reserved.
		4	0	Behavior when REF is unused: 0 = Logic "0", 1 = High impedance (tri-state).
		[3..2]	11	REF outputs power supply voltage: 00 = 01 = 1.8V, 10 = 2.5V, 11 = 3.3V.
		[1..0]	11	Reserved.
02	0x02	[7..0]	03-hex	Reserved.
03	0x03	[7..0]	34-hex	Reserved.
04	0x04	[7..0]	54-hex	Reserved.
05	0x05	7	1	Enable OUT1: 0 = Disabled (unused), 1 = Enabled.
		[6..4]	000	OUT1 configuration: 000 = LP-HCSL, Low-power HCSL. 001 = CMOS1, Single-ended CMOS on true output pin. 011 = LVDS. 100 = CMOS2, Single-ended CMOS on complementary output pin. 101 = CMOSD, Differential CMOS. 111 = CMOSP, Two single-ended CMOS outputs, in-phase. 010 and 110 are not used.
		[3..2]	00	OUT1 power supply voltage: 00 = 01 = 1.8V, 10 = 2.5V, 11 = 3.3V.
		[1..0]	11	Reserved.

Table 3. RAM Register Map (Cont.)

Register Address		Register Bit	Default	Function Description
Decimal	Hex			
06	0x06	7	0	Reserved.
		6	0	Behavior when OUT1 is unused: 0 = Logic "0", 1 = High impedance (tri-state).
		5	1	OUT1 LP-HCSL slew rate control: 0 = Slow, 1 = Fast.
		4	1	OUT1 LP-HCSL impedance control: 0 = 85Ω differential, 1 = 100Ω differential.
		[3..0]	0100	OUT1 LP-HCSL amplitude control: 650mVpp at 0000 – 950mVpp at 1111.
07	0x07	7	0	Reserved.
		[6..4]	101	OUT1 LVDS common mode control: 8μA at 000 – 11.5μA at 111.
		3	0	Reserved.
		[2..0]	100	OUT1 LVDS amplitude control: 30μA at 000 – 65μA at 111.
08	0x08	[7..0]	03-hex	Reserved.
09	0x09	[7..0]	34-hex	Reserved.
10	0x0A	[7..0]	54-hex	Reserved.
11	0x0B	7	1	Enable OUT0: 0 = Disabled (unused), 1 = Enabled.
		[6..4]	000	OUT0 configuration: 000 = LP-HCSL, Low-power HCSL. 001 = CMOS1, Single-ended CMOS on true output pin. 011 = LVDS. 100 = CMOS2, Single-ended CMOS on complementary output pin. 101 = CMOSD, Differential CMOS. 111 = CMOSP, Two single-ended CMOS outputs, in-phase. 010 and 110 are not used.
		[3..2]	00	OUT0 power supply voltage: 00 = 01 = 1.8V, 10 = 2.5V, 11 = 3.3V.
		[1..0]	11	Reserved.
12	0x0C	7	0	Reserved.
		6	0	Behavior when OUT0 is unused: 0 = Logic "0", 1 = High impedance (tri-state).
		5	1	OUT0 LP-HCSL slew rate control: 0 = Slow, 1 = Fast.
		4	1	OUT0 LP-HCSL impedance control: 0 = 85Ω differential, 1 = 100Ω differential.
		[3..0]	0100	OUT0 LP-HCSL amplitude control: 650mVpp at 0000 – 950mVpp at 1111.
13	0x0D	7	0	Reserved.
		[6..4]	101	OUT0 LVDS common mode control: 8μA at 000 – 11.5μA at 111.
		3	0	Reserved.
		[2..0]	100	OUT0 LVDS amplitude control: 30μA at 000 – 65μA at 111.

Table 3. RAM Register Map (Cont.)

Register Address		Register Bit	Default	Function Description
Decimal	Hex			
14	0x0E	7	1	Crystal oscillator LDO: 0 = Disabled, 1 = Enabled.
		6	0	Reserved.
		[5..0]	000000	Crystal oscillator X1 pin capacitance: Cap (pF) = 7.98 + 0.442 × Bits[5..0]. See section <a href="#">Crystal Load Capacitance Registers</a> for crystal oscillator load capacitance configuration.
15	0x0F	7	1	Crystal oscillator circuit: 0 = Disabled, 1 = Enabled.
		6	0	Reserved.
		[5..0]	000000	Crystal oscillator X2 pin capacitance: Cap (pF) = 7.98 + 0.442 × Bits[5..0].
16	0x10	[7..0]	83-hex	Reserved.
17	0x11	[7..0]	1A-hex	Reserved.
18	0x12	[7..0]	0C-hex	Reserved.
19	0x13	[7..0]	80-hex	Reserved.
20	0x14	[7..0]	00-hex	Reserved.
21	0x15	[7..0]	02-hex	Reserved.
22	0x16	[7..0]	96-hex	Reserved.
23	0x17	[7..0]	00-hex	Reserved.
24	0x18	[7..0]	00-hex	Reserved.
25	0x19	[7..0]	00-hex	Reserved.
26	0x1A	7	1	PLL, VCO band calibration start. Toggle to 0 and back to 1 to trigger a calibration. The calibration engages at the moment the bit moves from 0 to 1. The calibration finds the optimum VCO band for the current VCO frequency.
		6	0	Override VCO band: 0 = use calibrated VCO band, 1 = use VCO band value in bits [5..0].
		[5..0]	100000	VCO band value. See bit 6.
27	0x1B	7	1	Enable VCO: 0 = VCO disabled, 1 = VCO enabled.
		6	1	Enable charge pump: 0 = CP disabled, 1 = CP enabled.
		5	1	Enable PLL bias: 0 = PLL bias disabled, 1 = PLL bias enabled.
		4	1	Bypass 3 <sup>rd</sup> pole in loop filter: 0 = Use 3 <sup>rd</sup> pole, 1 = 3 <sup>rd</sup> pole bypassed.
		[3..0]	1100	Reserved.
28	0x1C	[7..4]	1010	Loop filter R-zero value.
		[3..0]	1111	Reserved.
29	0x1D	[7..0]	00-hex	Reserved.

Table 3. RAM Register Map (Cont.)

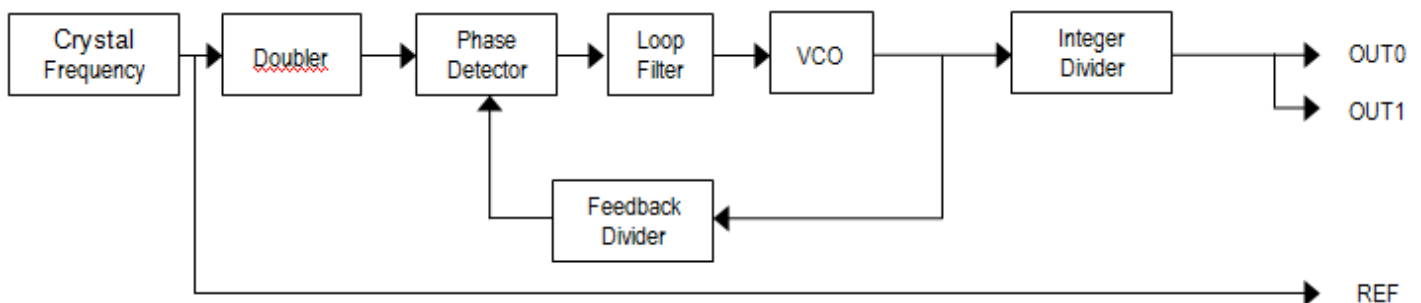
Register Address		Register Bit	Default	Function Description
Decimal	Hex			
30	0x1E	[7..4]	0000	Reserved.
		[3..0]	1010	Charge pump current, 0 to 750µA with step of 50µA.
31	0x1F	[7..0]	24-hex	PLL feedback divider value.
32	0x20	[7..0]	12-hex	Reserved.
33	0x21	[7..0]	18-hex	Integer output divider value, bits [7..0].
34	0x22	[7..4]	0000	Integer output divider value, bits [11..8].
		[3..0]	0000	Reserved.
35	0x23	[7..0]	00-hex	Reserved.
36	0x24	[7..0]	21-hex	Reserved.
37	0x25	7	0	Reserved.
		6	1	Enable Integer output divide: 0 = disabled, 1 = enabled.
		5	1	Enable crystal frequency doubler: 0 = disabled, 1 = enabled.
		[4..3]	00	Reserved.
		2	1	Integer output divide enable: 0 = disabled, 1 = enabled.
		[1..0]	01	Reserved.

<sup>1</sup> To be able to read this info, you already need to know the device address.

<sup>2</sup> These two bits show the configuration number 0–3 that will be loaded from OTP into registers at power up. When changing these bits through I<sup>2</sup>C you instruct the chip to load another configuration from OTP. This is useful for switching between OTP configurations when in I<sup>2</sup>C mode. This method is also used to step through each configuration for reading back OTP contents.

## Block Diagram

Figure 3. 9FGV1005 Block Diagram



### Equations:

$$FVCO = FCRYSTAL \times \text{Feedback Divider (see register 0x1F)}.$$

$$FOUT0 = FOUT1 = FVCO / \text{Integer Divider (see registers 0x21 and 0x22)}.$$

### Limits:

FCRYSTAL: 10MHz–40MHz

FVCO: 2300MHz–2600MHz

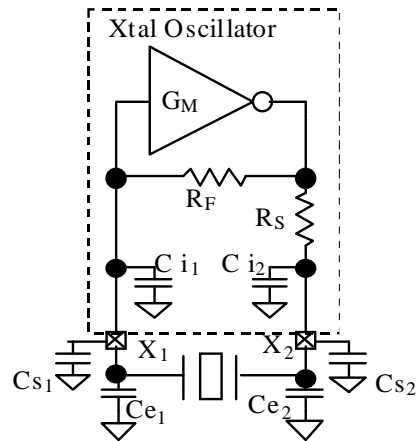
Integer Output Divider: 8–4095

Feedback Divider: 12–255

## Crystal Load Capacitance Registers

Registers 0x0E and 0x0F contain Crystal X1 and X2 Load capacitor settings that are used to add load capacitance to X1 and X2 (also known as XIN and XOUT) respectively.

Figure 4. Crystal Oscillator Circuit



Ci1 and Ci2 are on-chip capacitors that are programmable.

Cs is stray capacitance in the PCB and Ce is external capacitors for frequency fine tuning or for achieving load capacitance values beyond the range of the on-chip programmability. Consult the factory when adding Ce capacitors. The oscillator gain reduces with added capacitance and there may be crystal oscillator startup issues when adding too much capacitance.

All these capacitors combined make the load capacitance for the crystal.

Capacitance on pin XIN or X1:  $C_{x1} = C_{i1} + C_{s1} + C_{e1}$ .

Capacitance on pin XOUT or X2:  $C_{x2} = C_{i2} + C_{s2} + C_{e2}$ .

Total Crystal Load Capacitance  $C_L = C_{x1} \times C_{x2} / (C_{x1} + C_{x2})$ .

For optimum balance and oscillator gain it is recommended to design  $C_{x1} = C_{x2}$ . In that case  $C_L = C_{x1} / 2 = C_{x2} / 2$ .

The capacitance per pin X1 or X2 is:  $\text{Cap (pF)} = 7.98 + 0.442 \times \text{Bits}[5..0]$ .

This includes an estimated  $C_{s1} = C_{s2} = 1.0\text{pF}$ .

When designing  $C_{x1} = C_{x2}$ , the formula for CL is:  $C_L \text{ (pF)} = 3.99 + 0.221 \times \text{Bits}[5..0]$ .

The minimum  $C_L$  value at  $C_{x1} = C_{x2} = '00\ 0000'$ -binary = 3.99pF.

The maximum  $C_L$  value at  $C_{x1} = C_{x2} = '10\ 1111'$ -binary =  $3.99 + 0.221 \times 47 = 14.38\text{pF}$

Example: For a crystal  $C_L$  of 8pF, the registers can be programmed as follows:

$C_L \text{ (pF)} = 3.99 + 0.221 \times 18 = 7.97\text{pF}$  (nearest to 8.0pF).

So for  $C_L = 8\text{pF}$ , the recommended settings are  $C_{x1}[5..0] = C_{x2}[5..0] = 18$  or '01 0010'-binary.

Registers 0x0E = 0x0F = 92-hex (= '1001 0010' binary).



## Revision History

Revision Date	Description of Change
March 7, 2018	<ul style="list-style-type: none"><li>▪ Updated RAM Overview table.</li><li>▪ Updated RAM Register Map table (addresses 14, 15, 30, and 34).</li><li>▪ Updated Crystal Load Capacitance formulas.</li></ul>
October 11, 2017	Initial release.

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(Rev.1.0 Mar 2020)

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